BYQ30ED series

GENERAL DESCRIPTION

Glass passivated high efficiency rugged dual rectifier diodes in a plastic envelope suitable for surface mounting, featuring low forward voltage drop, ultra-fast recovery times and soft recovery characteristic. These devices can withstand reverse voltage transients and have guaranteed reverse surge and ESD capability. They are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and switching losses are essential.

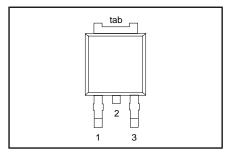
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{RRM}	BYQ30ED- Repetitive peak reverse voltage	100 100	150 150	200 200	V
V_{F} $I_{O(AV)}$	Forward voltage Output current (both diodes conducting)	0.95 16	0.95 16	0.95 16	V A
t _{rr} I _{RRM}	Reverse recovery time Repetitive peak reverse current per diode	25 0.2	25 0.2	25 0.2	ns A

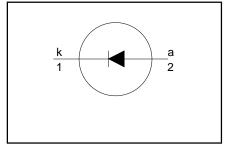
PINNING - SOT428

DESCRIPTION	
no connection	
cathode	
anode	
cathode	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
				-100	-150	-200	
V_{RRM}	Repetitive peak reverse voltage		-	100	150	200	V
V_{RWM}	Crest working reverse voltage		-	100	150	200	V
V_R	Continuous reverse voltage		-	100	150	200	V
I _{O(AV)}	Output current (both diodes	square wave	-		16		A
O(AV)	conducting) ¹	$\delta = 0.5$; $T_{mb} \le 104 ^{\circ}C$					
I _{O(RMS)}	RMS forward current		-		23		A
I _{FRM}	Repetitive peak forward current	$t = 25 \mu s; \delta = 0.5;$	-		16		A
1.	per diode	$T_{mb} \le 104 ^{\circ}C$.
I _{FSM}	Non-repetitive peak forward	t = 10 ms	-		100		A
	current per diode	t = 8.3 ms	-		110		A
		sinusoidal; with reapplied					
l ² t	12t for fusion	V _{RWM(max)}			EΟ		A ² s
l i	l ² t for fusing Repetitive peak reverse current	t = 10 ms	-		50 0.2		AS
I _{RRM}	per diode	$L_p = 2 \mu s, \ 0 = 0.001$	_		0.2		^
	Non-repetitive peak reverse	t _p = 100 μs	_		0.2		l a l
I _{RSM}	current per diode	μ – 100 μ0			0.2		'`
T_{stg}	Storage temperature		-40		150		°C ∣
T _i	Operating junction temperature		-		150		l °č ∣

¹ Neglecting switching and reverse current losses.

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ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _c	Electrostatic discharge capacitor voltage	Human body model; C = 250 pF; R = 1.5 kΩ	-	8	kV

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	per diode both diodes conducting minimum footprint, FR4 board	1 1 1	- - 50	3.0 2.5 -	K/W K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

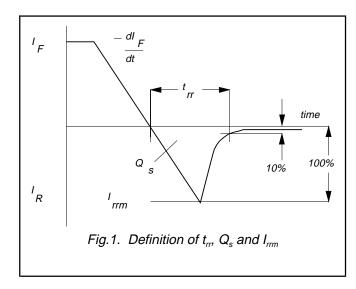
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage (per diode)	I _F = 8 A; T _i = 150°C I _F = 16 A; T _i = 150°C	-	0.83	0.95	V
	- "	$I_{\rm F} = 16 \text{ A}; T_{\rm i} = 150^{\circ}\text{C}$	-	1.0	1.15	V
		$I_{\rm F} = 16 \text{A};$	-	0.98	1.25	
l _R	Reverse current (per diode)	$V_R = V_{RWM}$; $T_i = 100 ^{\circ}C$	-	0.3	0.6	mA
		$V_R = V_{RWM}$	-	2	30	μΑ

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Q_s	Reverse recovery charge (per diode)	$I_F = 2 \text{ A}; V_R \ge 30 \text{ V}; -dI_F/dt = 20 \text{ A}/\mu\text{s}$	-	4	11	nC
t _{rr}	Reverse recovery time (per diode)	$I_F = 1 \text{ A}; V_R \ge 30 \text{ V};$ - $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	20	25	ns
I _{rrm}		$I_F = 1 \text{ A}; V_R \ge 30 \text{ V};$ - $dI_F/dt = 50 \text{ A/}\mu\text{s}; T_i = 100 ^{\circ}\text{C}$	-	1.0	2	Α
V_{fr}	Forward récovery voltage (per diode)	$I_F = 1 \text{ A}; dI_F/dt = 10' \text{ A/}\mu\text{s}$	-	1	-	V

BYQ30ED series



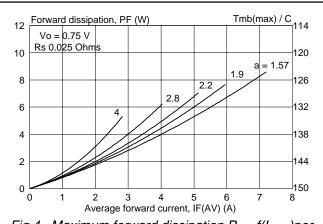
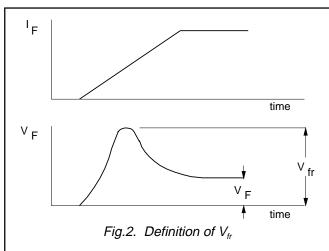
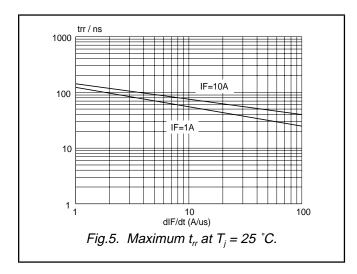
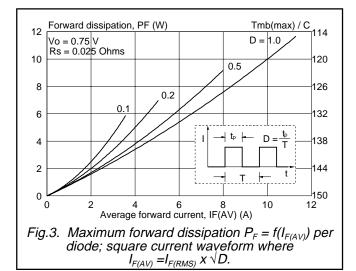
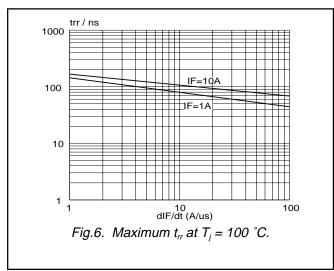


Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = f orm factor $= I_{F(RMS)} / I_{F(AV)}$.

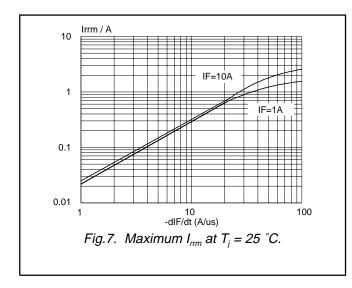


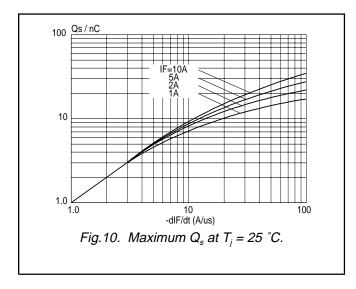


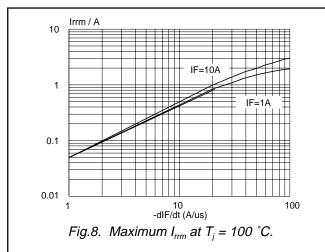


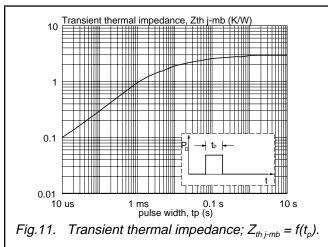


BYQ30ED series









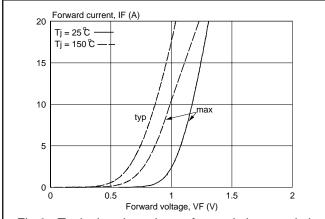
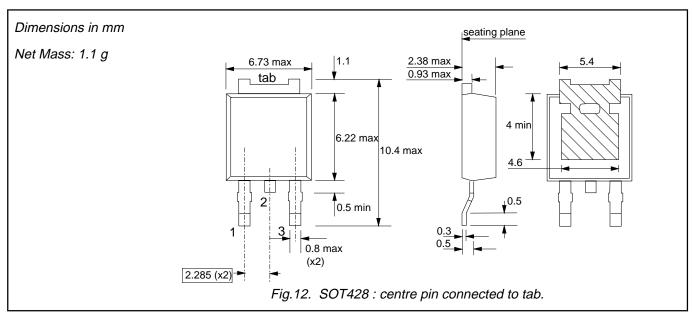


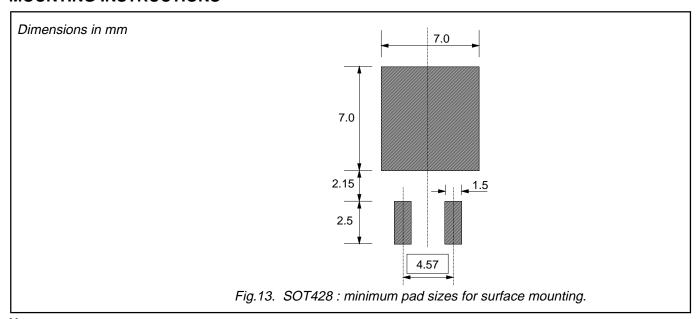
Fig.9. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

BYQ30ED series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

BYQ30ED series

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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